
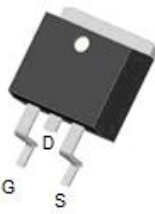
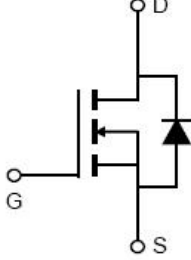


QIAOXIN N-Channel **Super Trench II** Power MOSFET

<p>Description</p> <p>The series of devices uses Super Trench II technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(on)}$ and Q_g. This device is ideal for high-frequency switching and synchronous rectification.</p> <p>Application</p> <ul style="list-style-type: none"> ● DC/DC Converter ● Ideal for high-frequency switching and synchronous rectification 	<p>General Features</p> <ul style="list-style-type: none"> ● $V_{DS} = 100V, I_D = 135A$ $R_{DS(on)} = 3.65m\Omega$, typical (TO-220)@ $V_{GS} = 10V$ $R_{DS(on)} = 3.5m\Omega$, typical (TO-263)@ $V_{GS} = 10V$ ● Excellent gate charge x $R_{DS(on)}$ product(FOM) ● Very low on-resistance $R_{DS(on)}$ ● 175 °C operating temperature ● Pb-free lead plating ● Pb-free Mold Compound
<div style="display: flex; justify-content: space-around;"> <div style="text-align: center;"> <p>TO-220</p>  </div> <div style="text-align: center;"> <p>TO-263</p>  </div> </div>	 <p>Schematic Diagram</p>

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VCRRP039N10M	VCRRP039N10M	TO-220	-	-	-
VCRRP039N10MD	VCRRP039N10MD	TO-263	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	135	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	108	A
Pulsed Drain Current	I_{DM}	540	A
Maximum Power Dissipation	P_D	220	W
Derating factor		1.47	W/ $^\circ C$
Single pulse avalanche energy (Note 1)	E_{AS}	730	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.68	$^\circ C/W$
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Electrical Characteristics (T_c=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
Off Characteristics							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	100		-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA	
On Characteristics							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =65A	TO-220	-	3.65	3.9	mΩ
			TO-263		3.5	3.9	mΩ
Gate resistance	R _G		-	1.5	-	Ω	
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =65A		90	-	S	
Dynamic Characteristics							
Input Capacitance	C _{iss}	V _{DS} =50V, V _{GS} =0V, F=1.0MHz	-	9500	-	PF	
Output Capacitance	C _{oss}		-	650	-	PF	
Reverse Transfer Capacitance	C _{rss}		-	40	-	PF	
Switching Characteristics (Note 2)							
Turn-on Delay Time	t _{d(on)}	V _{DD} =50V, I _D =65A V _{GS} =10V, R _G =1.6Ω	-	20	-	nS	
Turn-on Rise Time	t _r		-	11.5	-	nS	
Turn-Off Delay Time	t _{d(off)}		-	48	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Q _g	V _{DS} =50V, I _D =65A, V _{GS} =10V	-	125	-	nC	
Gate-Source Charge	Q _{gs}		-	40.5	-	nC	
Gate-Drain Charge	Q _{gd}		-	33	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =65A	-		1.2	V	
Diode Forward Current	I _S		-	-	135	A	
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	76	-	nS	
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs	-	150	-	nC	

Notes:

1. EAS condition : T_J=25°C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25Ω
2. Guaranteed by design, not subject to production
3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

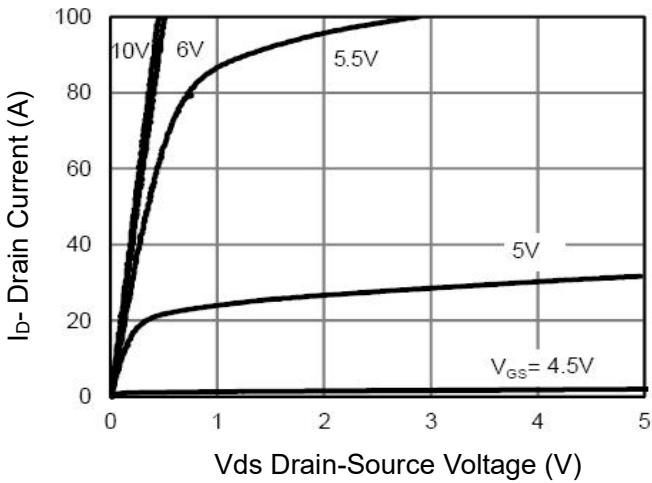


Figure 1 Output Characteristics

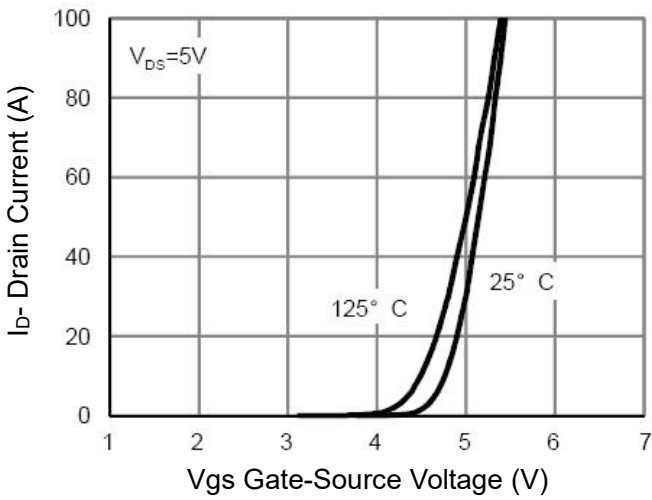


Figure 2 Transfer Characteristics

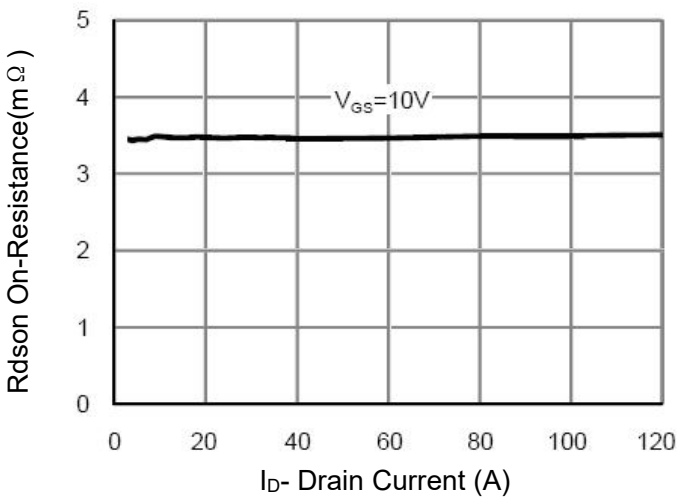


Figure 3 Rdson- Drain Current

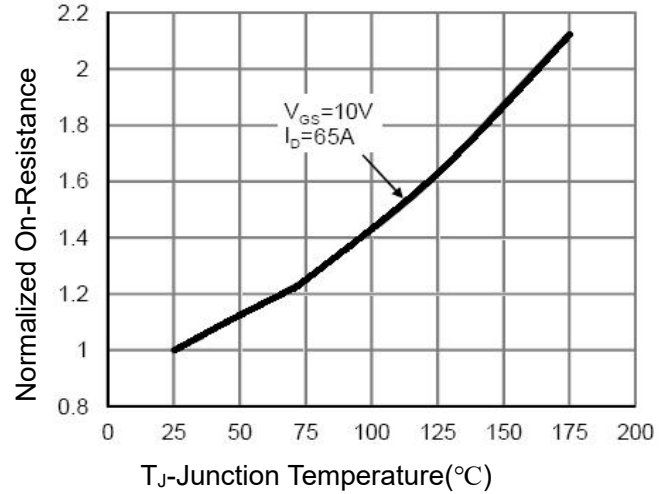


Figure 4 Rdson-Junction Temperature

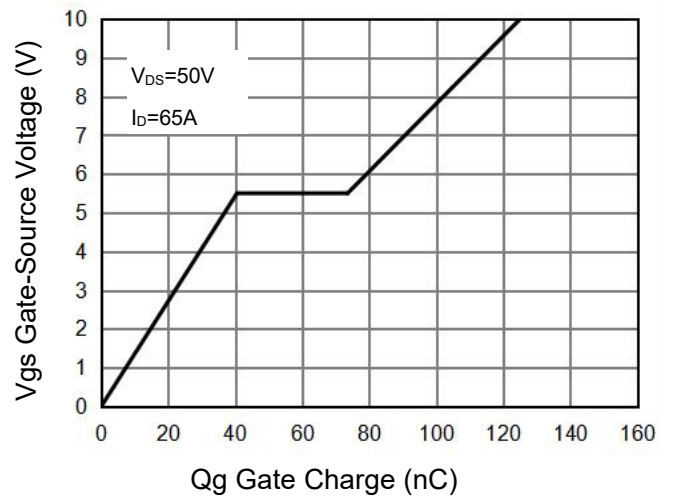


Figure 5 Gate Charge

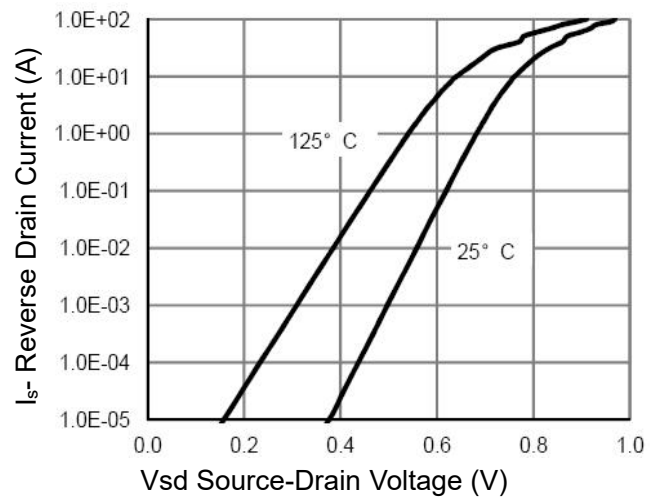


Figure 6 Source- Drain Diode Forward

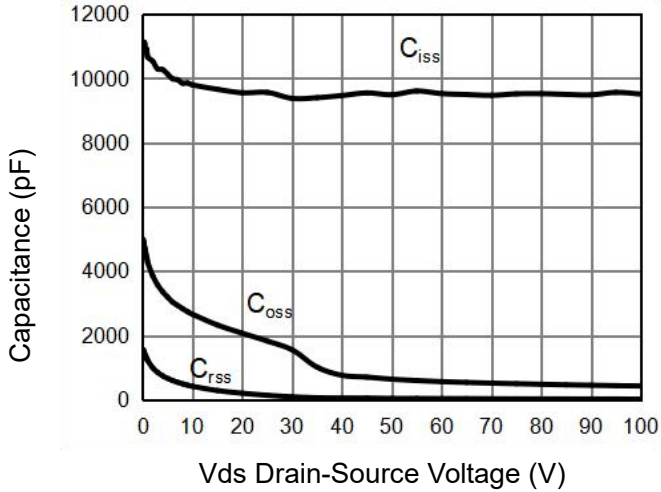


Figure 7 Capacitance vs Vds

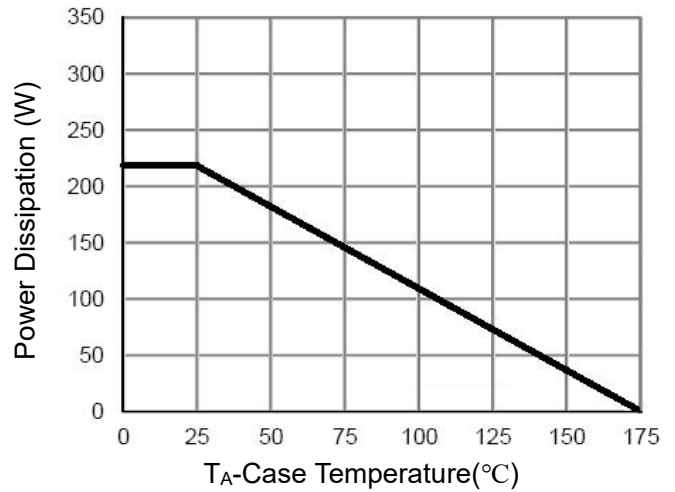


Figure 9 Power De-rating

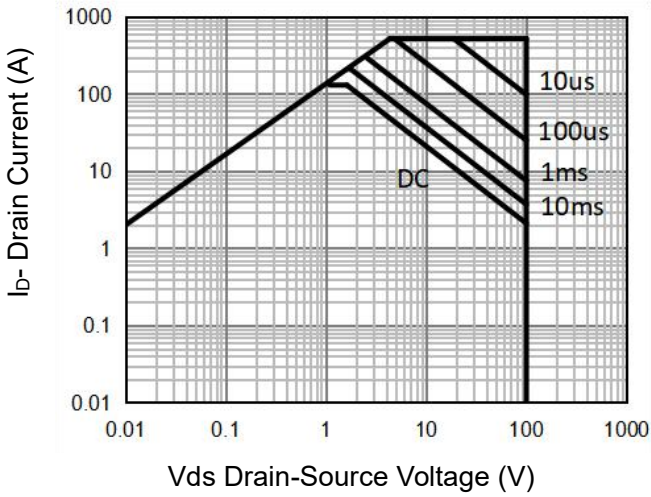


Figure 8 Safe Operation Area

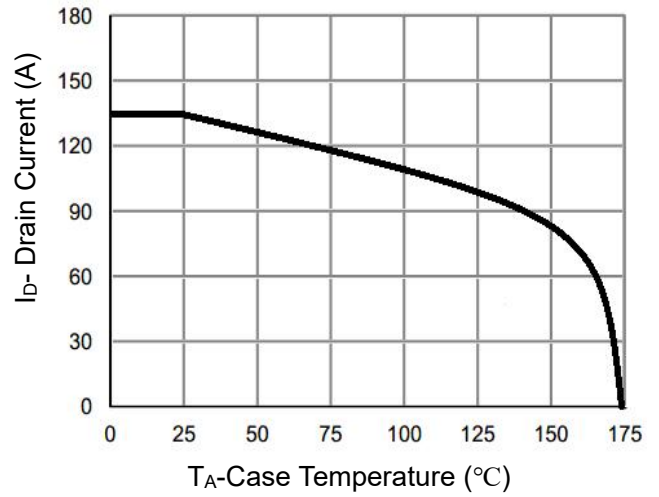


Figure 10 Current De-rating

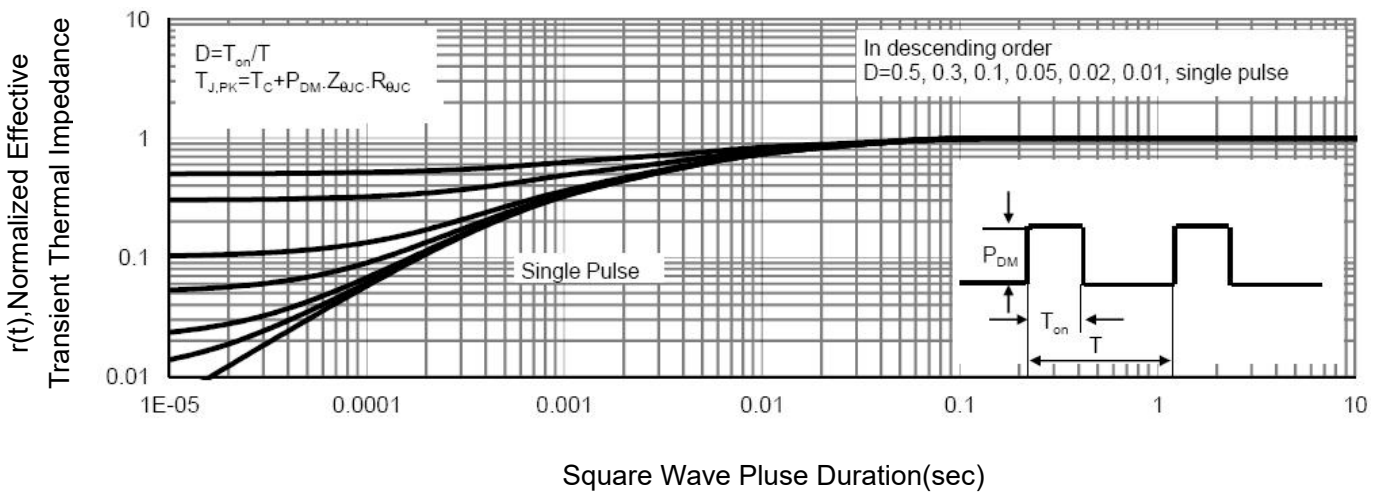
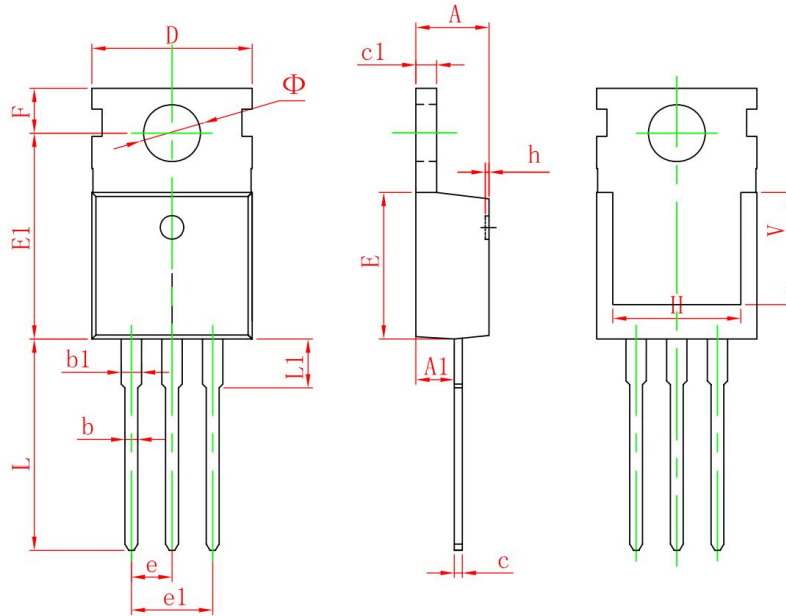


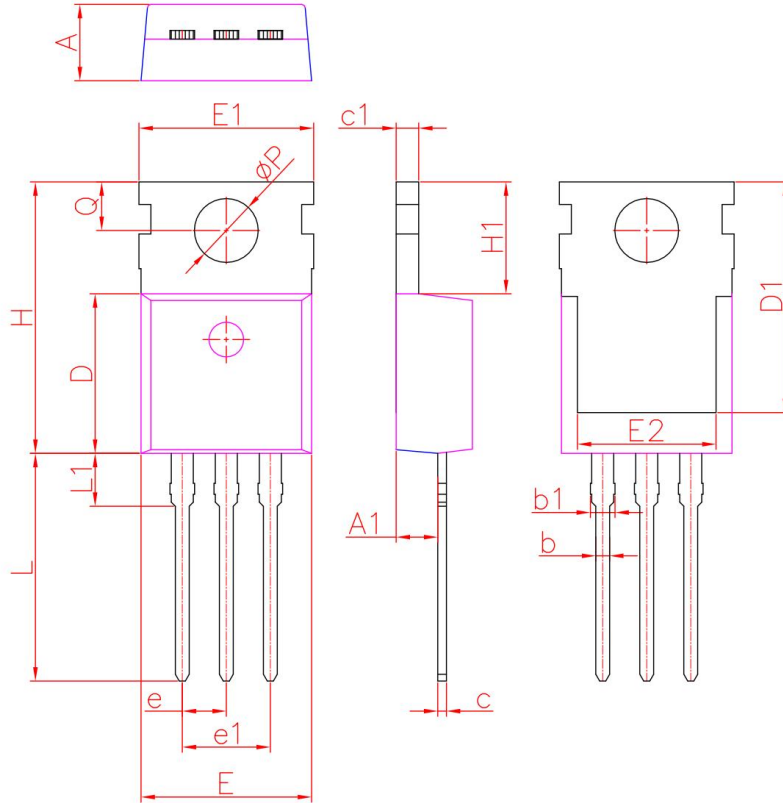
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L(C) Package Information



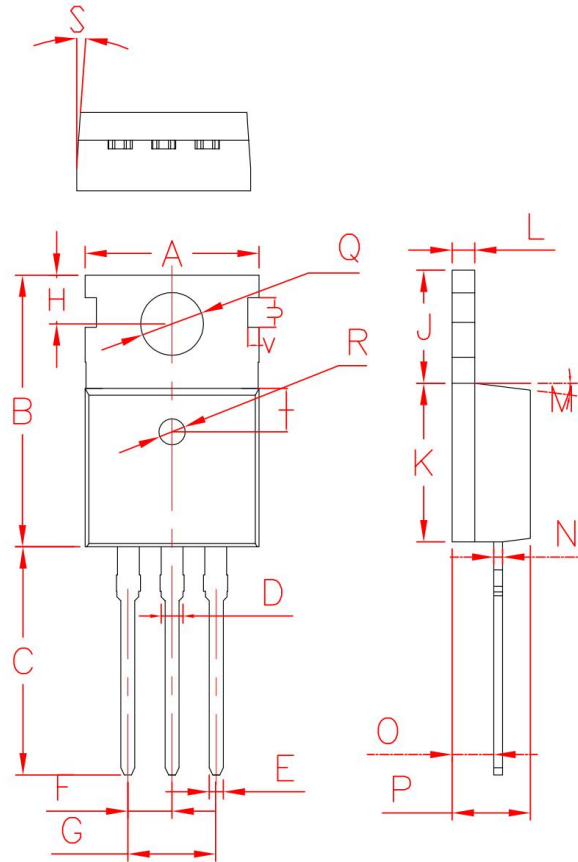
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150

TO-220-3L(E) Package Information



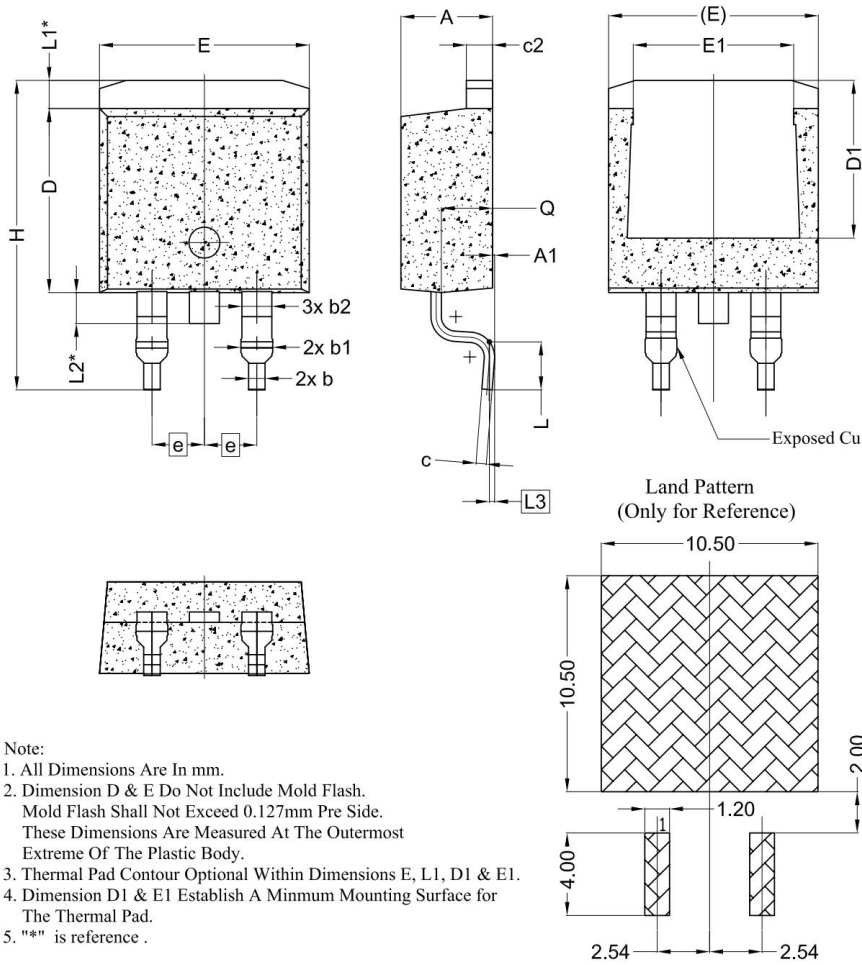
TO220			
DIM.	MIN.	NOM.	MAX.
A	4.20	4.40	4.60
A1	2.25	2.40	2.55
b	0.70	0.80	0.90
b1	1.17	1.27	1.37
c	0.33	0.50	0.65
c1	1.20	1.30	1.40
D	8.95	9.20	9.75
D1	13.10	13.30	13.50
E	9.74	9.84	10.04
E1	9.91	10.08	10.25
E2	7.90	8.00	8.10
e	2.54BSC		
e1	5.08BSC		
H	15.45	15.65	15.85
H1	6.30	6.45	6.60
L	12.90	13.13	13.40
L1	2.85	3.05	3.25
Q	2.65	2.80	2.95
øP	3.40	3.68	3.80
All dimensions in millimeters			

TO-220-3L(S) Package Information



Symbol	Min	Non	Max
A	9.80	10.00	10.20
B	15.40	15.60	15.80
C	12.75	13.10	13.45
D	1.18	1.31	1.44
E	0.70	0.80	0.90
F	2.42	2.54	2.66
G	4.84	5.08	5.32
H	2.73	2.80	2.87
I	2.40	2.50	2.60
J	6.40	6.50	6.60
K	9.00	9.10	9.20
L	1.29	1.30	1.32
M	6.5°	7.0°	7.5°
N	0.48	0.50	0.56
O	2.35	2.4	2.5
P	4.4	4.5	4.7
Q	3.5	3.6	3.63
R	1.4	1.5	1.6
S	2°	2.5°	3°
U	1.65	1.75	1.85
V	0.58	0.68	0.78

TO-263-2L Package Information



- Note:
1. All Dimensions Are In mm.
 2. Dimension D & E Do Not Include Mold Flash.
Mold Flash Shall Not Exceed 0.127mm Pre Side.
These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
 3. Thermal Pad Contour Optional Within Dimensions E, L1, D1 & E1.
 4. Dimension D1 & E1 Establish A Minmum Mounting Surface for The Thermal Pad.
 5. "*" is reference .

SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.70	0.80	0.90
b1	1.20	1.55	1.75
b2	1.20	1.45	1.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	2.54 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.50 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70

Attention

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